

NOTES:

Some of the problems can have multiple correct answers. One example is shown below.

SOLUTIONS:**Problem 1:**

The average thickness of a 12 inch (300 mm) wafer is 750-800 μm With a 150 μm saw

With n cuts $(n+1)$ wafers are obtained

$$(n + 1)(775 \mu m) + n(150 \mu m) = 2 m \rightarrow n = 2161$$

$$\text{Numbers of wafer} = 2161 + 1 = 2162$$

Answer can range from 2105 to 2222 depending on thickness value

Problem 2:

From the last page we find,

$$\text{Poly1 sheet resistance} = 7.7 \frac{\Omega}{\square}$$

$$\text{poly1-Insulator-M1 capacitance} = 64 \frac{aF}{\mu m^2}$$

$$\omega_{3dB} = \frac{1}{RC} = 2\pi f \rightarrow R = \frac{1}{2\pi f * c} = 19.89 * 10^6 \Omega$$

a. The minimum area of a poly1 resistor is

$$A_{Resistor} = \frac{19.89 * 10^6}{7.7} * 0.2^2 \mu m^2 = 103.32 * 10^3 \mu m^2$$

The minimum area of a Poly-M1 capacitor is

$$A_{Capacitor} = \frac{8pF}{64 \frac{aF}{\mu m^2}} = 125 * 10^3 \mu m^2$$

$$\text{Total Area } A = A_{Res} + A_{Cap} = 103.32 * 10^3 + 125 * 10^3 = 228.32 * 10^3 \mu m^2$$

b) We will start with the minimized size resistor has a sheet of x ■ and the capacitor has an area of $y \mu m^2$.

$$\text{Total area } A = (0.2 * 0.2) * x + y = 0.04x + y$$

$$\frac{1}{RC} = \omega_{3dB} = 2\pi f \rightarrow RC = \frac{1}{2\pi f} = 0.0001592 \text{ Hz}$$

$$(x * 7.7)(64 * 10^{-18} * y) = 0.0001592 \rightarrow y = \frac{3.23 * 10^{11}}{x}$$

$$A = 0.04x + \left(\frac{3.23 * 10^{11}}{x} \right) \rightarrow A_{min} \text{ when } 0.04x = \frac{3.23 * 10^{11}}{x}$$

$$x = 2.84 * 10^6 \rightarrow y = \frac{7.952 * 10^{12}}{7.0495 * 10^6} = 0.114 * 10^6 \mu m^2$$

$$R = 2.84 * 10^6 * 7.7 = 55.2 * 10^6 = \mathbf{21.87 \text{ M}\Omega}$$

$$C = 0.114 * 10^6 * 64 * 10^{-18} = 7.28 * 10^{-12} = \mathbf{7.28 \text{ pF}}$$

Problem 3:

- Length = $1 \mu m$, width = $2 \mu m$
- Positive photoresist overexposed decreases the size, under-etching increases the size
Length = $1 - 0.1 + 0.1 = \mathbf{1.0 \mu m}$
Width is unchanged.
- Overexposing negative photoresist increases the size, under-etching negative photoresist increases size
Length = $1 + 0.1 + 0.1 = \mathbf{1.2 \mu m}$

Problem 4:

Approximately 53% of the oxide grows above the wafer, and 47% grows into the wafer.

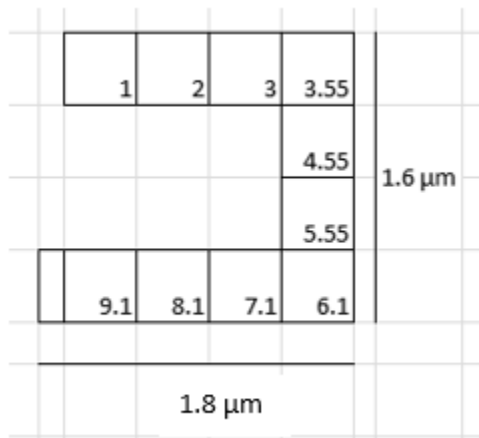
$$\text{The increased wafer height } W_{height} = 0.53 * 5000 = \mathbf{2650 \text{ \AA}}$$

Problem 5:

Sheet Resistance of poly is $317.1 \Omega/\blacksquare \Rightarrow \frac{3000}{317.1} = 9.46$

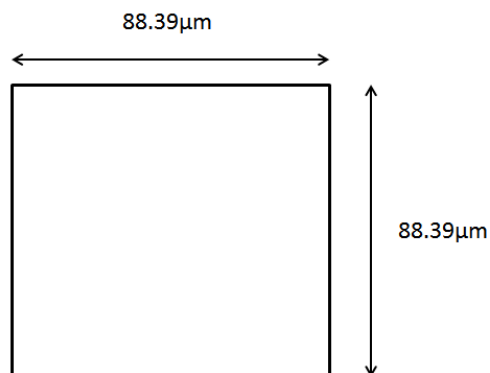
Use $0.4 \mu\text{m}$ by $0.4 \mu\text{m}$ squares with the last square being $0.2 \mu\text{m}$ by $0.4 \mu\text{m}$ (counts as 1/2 of square).

$$8 + 0.5 + (2 * 0.55) = 9.6 \blacksquare = 3044.2 \Omega$$

**Problem 6:**

Using poly and Metal1 $\Rightarrow 64 \text{ aF}/\mu\text{m}^2$

$$A_c = \frac{0.5 * 10^{-12} F}{64 * 10^{-18} F/\mu\text{m}^2} = 7812.5 \mu\text{m}^2 \Rightarrow \sqrt{A_c} = 88.39 \mu\text{m}$$



Problem 7:

$$R(320) = 4534 * \left(1 + (320 - 250) * \left(\frac{1200}{10^6} \right) \right) = 4914 \, \Omega$$

Problem 8:

Number of ■ = 100

Sheet resistance of Poly = $7.7 \, \Omega/\blacksquare$

Resistance = $100 * 7.7 = 770 \, \Omega$

Area = $100 \, \mu\text{m}^2$

Poly-Substrate = $103 \, \text{aF}/\mu\text{m}^2$

M1-Poly = $64 \, \text{aF}/\mu\text{m}^2$

$$C_{\text{Poly-Substrate}} = 100 \, \mu\text{m}^2 * 103 \frac{\text{aF}}{\mu\text{m}^2} = 10.3 \, \text{fF}$$

$$C_{\text{M1-Poly}} = 100 \, \mu\text{m}^2 * 64 \frac{\text{aF}}{\mu\text{m}^2} = 6.4 \, \text{fF}$$

Problem 9 :

Half adder code:

Ln#	
1	<code>`timescale 1ns / 1ps</code>
2	
3	<code>module Halfadder (iA, iB, oSum, oCarry);</code>
4	<code>input iA, iB; //defining inputs</code>
5	<code>output oSum, oCarry; //defining outputs</code>
6	
7	<code>assign oSum = iA^iB; //sum is equal to A xor B</code>
8	<code>assign oCarry = iA & iB; //carry is equal to A and B</code>
9	
10	<code>endmodule </code>

Test Bench:

```
h /home/falegria/ee330/Half_adder_tb.v - Default
Ln#
1 `timescale 1ns / 1ps
2 module half_adder_tb ();
3     reg A,B;
4     wire Sum, Carry;
5     Halfadder uut (.iA(A), .iB(B), .oSum(Sum), .oCarry(Carry)); //unit under
6
7     initial
8     begin //begin setting bits (basically recreating the truth table)
9
10
11         A = 1'b0;
12         B = 1'b0;
13     end
14     initial
15     begin
16         #10//timestamp to wait 35ns
17
18         A = 1'b0;
19         B = 1'b1;
20
21         #10 //timestamp to wait 35ns
22
23         A = 1'b1;
24         B = 1'b0;
25
26         #10 //timestamp to wait 35ns
27
28         A = 1'b1;
29         B = 1'b1;
30
31         #10 ;//timestamp to wait 35ns
32     end
33 endmodule
```

Ignore timestamp comments

Waveform:

